

The listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1.-13. (Canceled)

14. (New) A luminescent device comprising:

a thin film transistor provided over an insulating surface;
a luminescent element electrically connected with said thin film transistor,
comprising:

an organic compound layer containing an alkaline metal;
an anode; and
a cathode; and

at least one insulating layer provided between said thin film transistor and said luminescent element,

wherein said insulating layer is capable of adsorbing said alkaline metal.

15. (New) A device according to claim 14, wherein said at least one insulating layer comprises a silicon nitride film containing fluorine at a concentration of $1 \times 10^{19}/\text{cm}^3$ or more.

16. (New) A device according to claim 14, wherein said at least one insulating layer comprises an organic resin film containing a particle comprising an antimony (Sb) compound, a tin (Sn) compound, or indium (In) compound.

17. (New) A device according to claim 14, wherein said at least one insulating layer comprises a laminated layer of a silicon nitride film containing fluorine at a

concentration of $1 \times 10^{19}/\text{cm}^3$ or more and an organic resin film containing a particle comprising an antimony (Sb) compound, a tin (Sn) compound, or indium (In) compound.

18. (New) A device according to claim 14, wherein said insulating layer comprises a silicon oxynitride film or a silicon oxide film containing fluorine at a concentration of $1 \times 10^{19}/\text{cm}^3$ or more.

19. (New) A luminescent device comprising:
a thin film transistor provided over an insulating surface;
a luminescent element electrically connected with said thin film transistor,
comprising:

- an organic compound layer;
- an anode;
- a buffer layer containing an alkaline metal; and
- a cathode; and

at least one insulating layer provided between said thin film transistor and said luminescent element,

wherein said insulating layer is capable of adsorbing said alkaline metal.

20. (New) A device according to claim 19, wherein said at least one insulating layer comprises a silicon nitride film containing fluorine at a concentration of $1 \times 10^{19}/\text{cm}^3$ or more.

21. (New) A device according to claim 19, wherein said at least one insulating layer comprises an organic resin film containing a particle comprising an antimony (Sb) compound, a tin (Sn) compound, or indium (In) compound.

22. (New) A device according to claim 19, wherein said at least one insulating layer comprises a laminated layer of a silicon nitride film containing fluorine at a concentration of $1 \times 10^{19}/\text{cm}^3$ or more and an organic resin film containing a particle comprising an antimony (Sb) compound, a tin (Sn) compound, or indium (In) compound.

23. (New) A device according to claim 19, wherein said insulating layer comprises a silicon oxynitride film or a silicon oxide film containing fluorine at a concentration of $1 \times 10^{19}/\text{cm}^3$ or more.

24. (New) A luminescent device comprising:

a thin film transistor provided over an insulating surface;

a luminescent element electrically connected with said thin film transistor, comprising:

an organic compound layer;

an anode; and

a cathode containing an alkaline-earth metal; and

at least one insulating layer provided between said thin film transistor and said luminescent element,

wherein said insulating layer is capable of adsorbing said alkaline-earth metal.

25. (New) A device according to claim 24, wherein said at least one insulating layer comprises a silicon nitride film containing fluorine at a concentration of $1 \times 10^{19}/\text{cm}^3$ or more.

26. (New) A device according to claim 24, wherein said at least one insulating layer comprises an organic resin film containing a particle comprising an antimony (Sb) compound, a tin (Sn) compound, or indium (In) compound.

27. (New) A device according to claim 24, wherein said at least one insulating layer comprises a laminated layer of a silicon nitride film containing fluorine at a concentration of $1 \times 10^{19}/\text{cm}^3$ or more and an organic resin film containing a particle comprising an antimony (Sb) compound, a tin (Sn) compound, or indium (In) compound.

28. (New) A device according to claim 24, wherein said insulating layer comprises a silicon oxynitride film or a silicon oxide film containing fluorine at a concentration of $1 \times 10^{19}/\text{cm}^3$ or more.

29. (New) A luminescent device comprising:
a thin film transistor provided over an insulating surface;
a luminescent element electrically connected with said thin film transistor,
comprising:
an organic compound layer containing an alkaline-earth metal;
an anode; and
a cathode;
at least one insulating layer provided between said thin film transistor and said luminescent element,
wherein said insulating layer is capable of adsorbing said alkaline-earth metal.

30. (New) A device according to claim 29, wherein said at least one insulating layer comprises a silicon nitride film containing fluorine at a concentration of $1 \times 10^{19}/\text{cm}^3$ or more.

31. (New) A device according to claim 29, wherein said at least one insulating layer comprises an organic resin film containing a particle comprising an antimony (Sb) compound, a tin (Sn) compound, or indium (In) compound.

32. (New) A device according to claim 29, wherein said at least one insulating layer comprises a laminated layer of a silicon nitride film containing fluorine at a concentration of $1 \times 10^{19}/\text{cm}^3$ or more and an organic resin film containing a particle comprising an antimony (Sb) compound, a tin (Sn) compound, or indium (In) compound.

33. (New) A device according to claim 29, wherein said insulating layer comprises a silicon oxynitride film or a silicon oxide film containing fluorine at a concentration of $1 \times 10^{19}/\text{cm}^3$ or more.

34. (New) A luminescent device comprising:

a thin film transistor provided over an insulating surface of a substrate;

a luminescent element electrically connected with said thin film transistor, comprising:

an organic compound layer;

an anode;

a buffer layer containing an alkaline-earth metal; and

a cathode; and

at least one insulating layer provided between said thin film transistor and said luminescent element

wherein said insulating layer is capable of adsorbing said alkaline-earth metal.

35. (New) A device according to claim 34, wherein said at least one insulating layer comprises a silicon nitride film containing fluorine at a concentration of $1 \times 10^{19}/\text{cm}^3$ or more.

36. (New) A device according to claim 34, wherein said at least one insulating layer comprises an organic resin film containing a particle comprising an antimony (Sb) compound, a tin (Sn) compound, or indium (In) compound.

37. (New) A device according to claim 34, wherein said at least one insulating layer comprises a laminated layer of a silicon nitride film containing fluorine at a concentration of $1 \times 10^{19}/\text{cm}^3$ or more and an organic resin film containing a particle comprising an antimony (Sb) compound, a tin (Sn) compound, or indium (In) compound.

38. (New) A device according to claim 34, wherein said insulating layer comprises a silicon oxynitride film or a silicon oxide film containing fluorine at a concentration of $1 \times 10^{19}/\text{cm}^3$ or more.